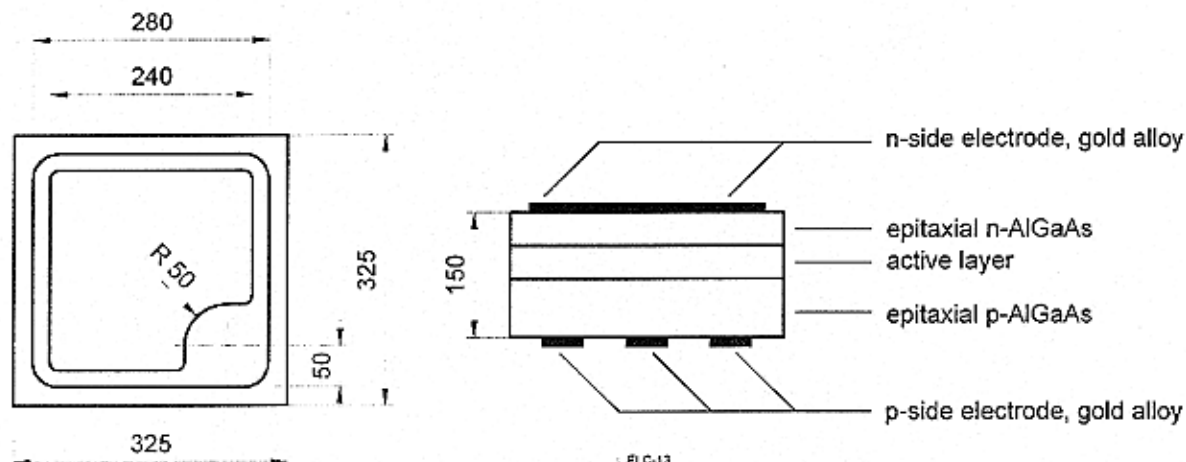


Radiation	Type	Technology	Electrodes
Infrared	ELC-840-25	AlGaAs/AlGaAs DHS	N (cathode) up

Outline (dimensions in microns)**Optical and Electrical Characteristics**

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.40	1.6	V
Reverse voltage	$I_R = 100 \mu\text{A}$	V_R	5			V
Radiant power	$I_F = 20 \text{ mA}$	Φ_e	1.65	1.85		mW
Radiant power	$I_F = 50 \text{ mA}$	Φ_e	4.0	4.4		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p		840		nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		40		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		25 ?		ns

Labeling

Type	Lot N°	Φ_e (typ, min, max)	Quantity
ELC-840-25			

Packing

Chips on adhesive film with wire-bond side on top